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June 2014



FQA90N08

N-Channel QFET® MOSFET

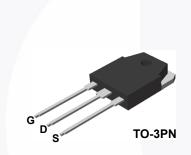
80 V, 90 A, 16 mΩ

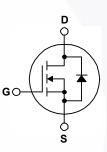
Description

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, DC motor control, and variable switching power applications.

Features

- 90 A, 80 V, R_{DS(on)} = 16 m Ω (Max) @V_{GS} = 10 V, I_D = 45 A
- Low Gate Charge (Typ. 84 nC)
- Low Crss (Typ. 200 pF)
- 100% Avalanche Tested
- 175°C Maximum Junction Temperature Rating





Absolute Maximum Ratings T_C = 25°C unless otherwise noted

Symbol	Parameter		FQA90N08	Unit	
V _{DSS}	Drain-Source Voltage		80	V	
D	Drain Current - Continuous (T _C = 25°C)	90	A	
	- Continuous (T _C = 100°	63.5	A		
DM	Drain Current - Pulsed	(Note 1)	360	A	
/ _{GSS}	Gate-Source Voltage		± 25	V	
AS	Single Pulsed Avalanche Energy	(Note 2)	1360	mJ A	
AR	Avalanche Current	(Note 1)	90		
AR	Repetitive Avalanche Energy	(Note 1)	21.4	mJ	
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	6.5	V/ns	
D	Power Dissipation ($T_C = 25^{\circ}C$)		214	W	
	- Derate above 25°C		1.43	W/°C	
Γ _J , T _{STG}	Operating and Storage Temperature Range		-55 to +175	°C	
۲ _L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds		300	°C	

Thermal Characteristics

Symbol	Parameter	FQA90N08	Unit	
$R_{ extsf{ heta}JC}$	Thermal Resistance, Junction-to-Case, Max.	0.7	°C/W	
$R_{ extsf{ heta}JA}$	Thermal Resistance, Junction-to-Ambient, Max.	40	°C/W	

Device MarkingDeviceFQA90N08FQA90N08		PackageReel SizeTO-3PN-		Tape Width		th C	Quantity	
						30		
Electric	cal Cha	racteristics T _c = 25°C	unless otherwise noted					
Symbol	ool Parameter Te		Test Cor	Test Conditions		Тур	Мах	Unit
Off Cha	racterist	ics						
BV _{DSS}		rce Breakdown Voltage	V _{GS} = 0 V, I _D = 250 μA		80			V
ΔBV_{DSS} / $\Delta T_{.1}$		n Voltage Temperature	$I_D = 250 \mu\text{A}$, Referenced to 25°C			0.1		V/°C
I _{DSS}	Zero Gate Voltage Drain Current		V _{DS} = 100 V, V _{GS} = 0 V				1	μA
			$V_{DS} = 80 \text{ V}, \text{ T}_{C} = 150^{\circ}\text{C}$				10	μA
I _{GSSF}	Gate-Body	/ Leakage Current, Forward	V _{GS} = 25 V, V _{DS} = 0 V				100	nA
I _{GSSR}	Gate-Body	/ Leakage Current, Reverse	$V_{GS} = -25 V, V_{DS} = 0 V$				-100	nA
On Cha	racterist	ics						
V _{GS(th)}	Gate Thre	shold Voltage	$V_{DS} = V_{GS}, I_D = 2$	250 μΑ	2.0		4.0	V
R _{DS(on)}	Static Drai On-Resist		V _{GS} = 10 V, I _D =	45 A		0.012	0.016	Ω
9 _{FS}	Forward T	ransconductance	V _{DS} = 30 V, I _D =	45 A		52		S
-		cteristics				I	Γ	
C _{iss}	Input Cap		V_{DS} = 25 V, V_{GS}	V_{DS} = 25 V, V_{GS} = 0 V,		2500	3250	pF
C _{oss}	Output Ca		f = 1.0 MHz			900	1170	pF
C _{rss}	Reverse T	ransfer Capacitance				200	260	pF
Switchi	ing Chara	acteristics						
t _{d(on)}	Turn-On D	elay Time	V _{DD} = 40 V, I _D =	90 A		30	70	ns
t _r	Turn-On F	Rise Time	$R_{G} = 25 \Omega$	007 Q		360	730	ns
t _{d(off)}	Turn-Off D	elay Time				100	210	ns
t _f	Turn-Off F	all Time		(Note 4)		160	330	ns
Qg	Total Gate	Charge	V _{DS} = 64 V, I _D =	90 A,		84	110	nC
Q _{gs}	Gate-Sour	ce Charge	V _{GS} = 10 V			17		nC
Q _{gd}	Gate-Drai	n Charge		(Note 4)		42		nC
Drain-S	ource Di	ode Characteristics a	nd Maximum R	Ratings				
I _s	ource Diode Characteristics and Maximum Ratings Maximum Continuous Drain-Source Diode Forward Current						90	Α
I _{SM}		Pulsed Drain-Source Diode F					360	A
V _{SD}		rce Diode Forward Voltage	$V_{GS} = 0 V, I_{S} = 9$	0 A			1.5	V
t _{rr}		Recovery Time	$V_{GS} = 0 V, I_S = 9$			87		ns
11			- GS - 7, 1S - 0	,		5.		110

 Q_{rr}

Reverse Recovery Charge

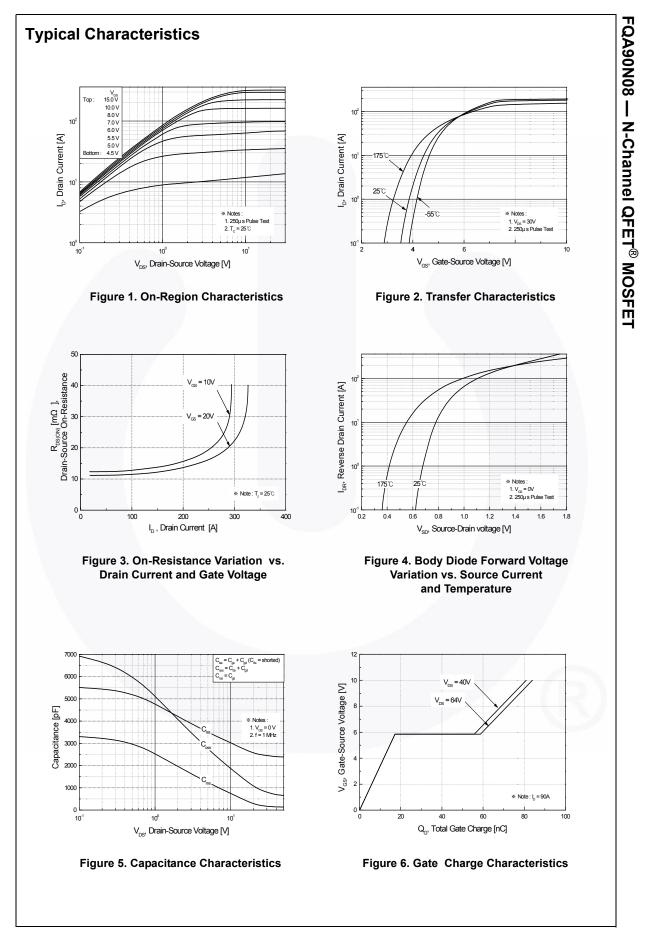
Notes: 1. Repetitive Rating : Pulse width limited by maximum junction temperature 2. L = 0.23mH, I_{AS} = 90A, V_{DD} = 25V, R_G = 25 Ω , Starting T_J = 25°C 3. $I_{SD} \le$ 90A, di/dt \le 300A/ μ s, $V_{DD} \le$ BV_{DSS}, Starting T_J = 25°C 4. Essentially independent of operating temperature

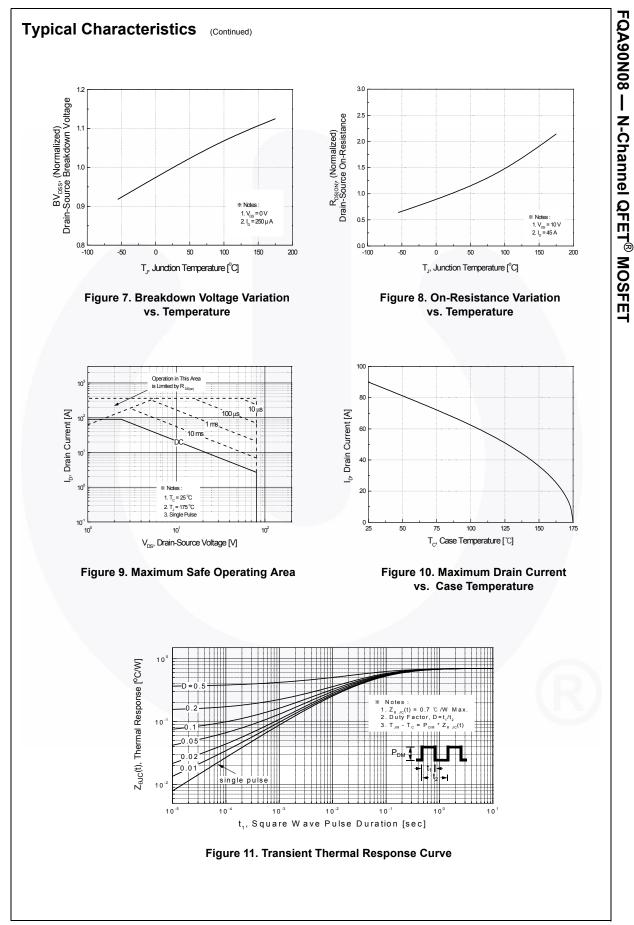
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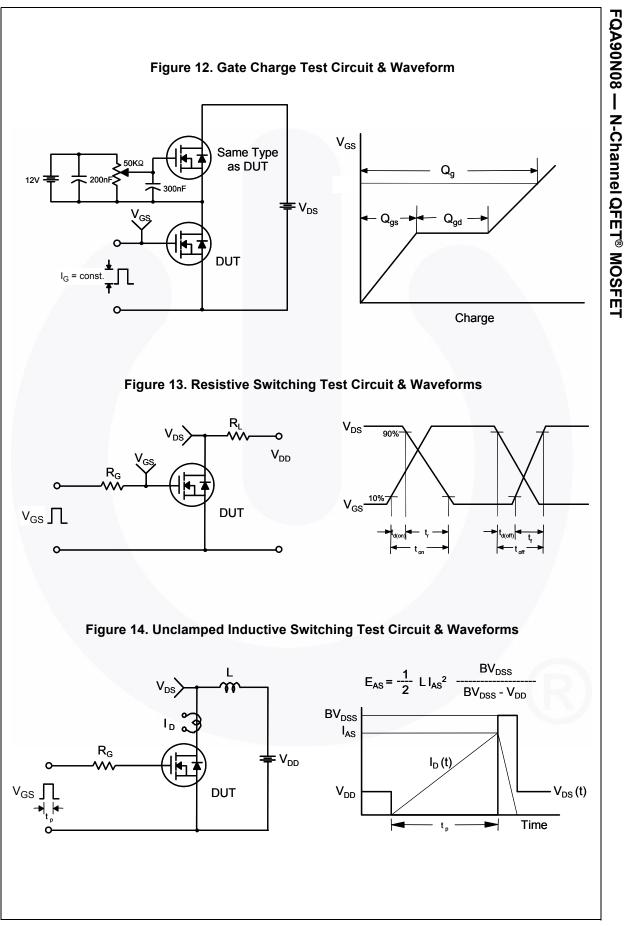
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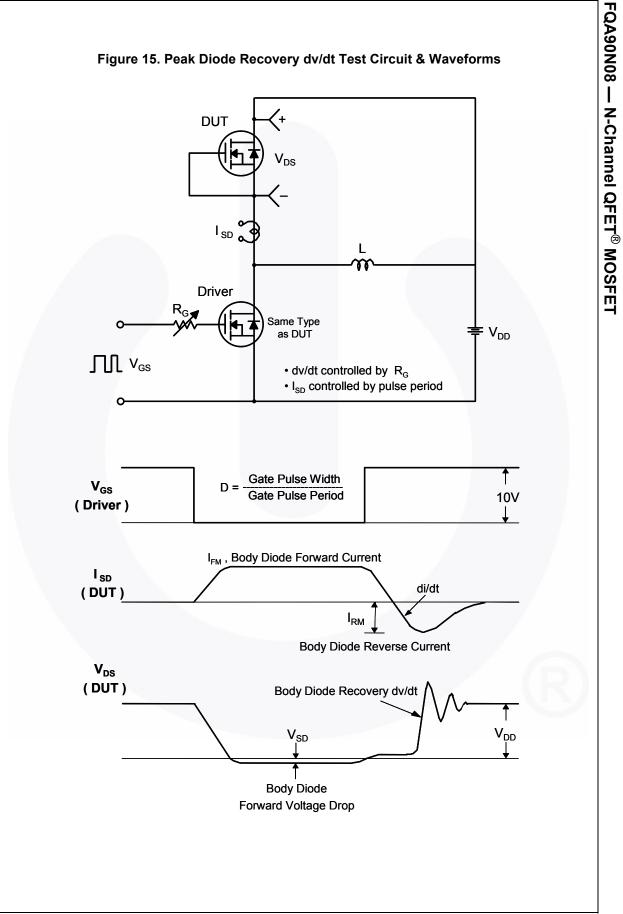
nC

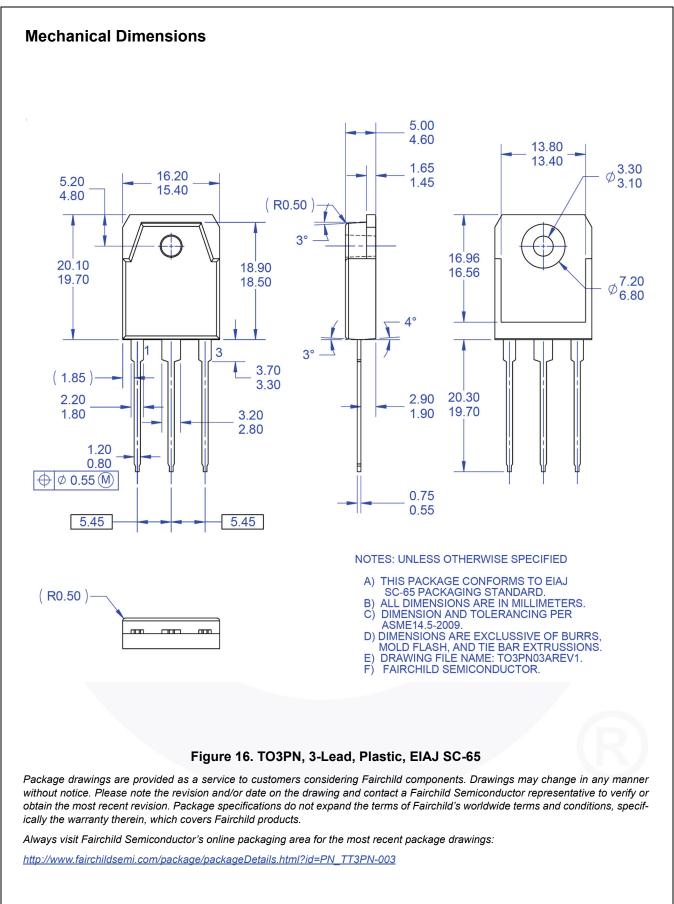
 $dI_F / dt = 100 \text{ A/}\mu\text{s}$













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